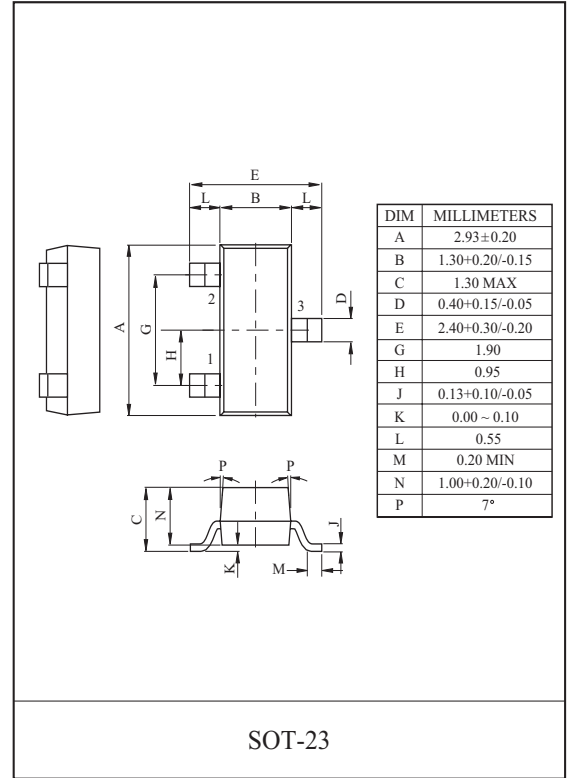


General Description

This Trench MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for portable equipment.

FEATURES

- $V_{DSS}=30V$, $I_D=4.2A$
- Drain-Source ON Resistance
 $R_{DS(ON)}=42m$ (Max.) @ $V_{GS}=10V$
 $R_{DS(ON)}=54m$ (Max.) @ $V_{GS}=4.5V$
- Super High Dense Cell Design
- ESD protected

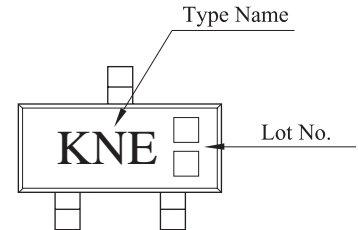


MAXIMUM RATING (Ta=25 °C)

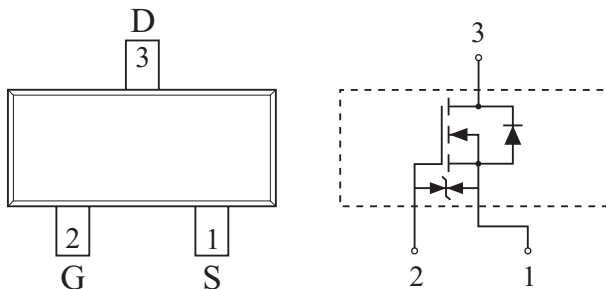
CHARACTERISTIC	SYMBOL	N-Ch	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC@ $T_A=25$	4.2	A
	DC@ $T_A=70$	3.3	
	Pulsed	I_{DP}^*	
Drain-Source-Diode Forward Current	I_S	1.04	A
Drain Power Dissipation	$T_A=25$	1.25	W
	$T_A=70$	0.8	
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance, Junction to Ambient	R_{thJA}^*	100	/W

Note > *Surface Mounted on 2" x 2" FR4 Board, t = 10sec

Marking



PIN CONNECTION (TOP VIEW)



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ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	BV_{DSS}	$I_{DS}=250\ \mu A, V_{GS}=0V,$	30	-	-	V	
Drain Cut-off Current	I_{DSS}	$V_{GS}=0V, V_{DS}=30V$	-	-	0.5	μA	
		$V_{GS}=0V, V_{DS}=30V, T_j=55$	-	-	10		
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$	-	-	± 10	μA	
Gate Threshold Voltage	V_{th}	$V_{DS}=V_{GS}, I_D=250\ \mu A$	1.0	-	1.8	V	
Drain-Source ON Resistance	$R_{DS(ON)}^*$	$V_{GS}=10V, I_D=4.2A$	-	32	42	m	
		$V_{GS}=4.5V, I_D=2A$	-	40	54		
On-State Drain Current	$I_{D(ON)}^*$	$V_{GS}=5V, V_{DS}=4.5V$	10	-	-	A	
Forward Transconductance	g_{fs}^*	$V_{DS}=5V, I_D=4.2A$	-	13	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{DS}=15V, f=1MHz, V_{GS}=0V$	-	310	-	pF	
Output Capacitance	C_{oss}		-	80	-		
Reverse Transfer Capacitance	C_{rss}		-	40	-		
Total Gate Charge	Q_g^*	$V_{DS}=15V, V_{GS}=10V, I_D=4.2A$	$V_{gs}=10V$	-	7.2	-	nC
			$V_{gs}=4.5V$	-	3.5	-	
Gate-Source Charge	Q_{gs}^*		-	0.8	-		
Gate-Drain Charge	Q_{gd}^*		-	1.8	-		
Turn-On Delay Time	$t_{d(on)}^*$	$V_{DD}=15V, V_{GS}=10V$ $I_D=4.2A, R_G=6$	-	7.0	-	ns	
Turn-On Rise Time	t_r^*		-	5.3	-		
Turn-Off Delay Time	$t_{d(off)}^*$		-	32.0	-		
Turn-Off Fall Time	t_f^*		-	3.1	-		
Source-Drain Diode Ratings							
Source-Drain Forward Voltage	V_{SDF}^*	$V_{GS}=0V, I_{DR}=1A$	-	0.8	1.2	V	
Reverse Recovery Time	t_{rr}	$I_S=4.2A, V_{GS}=0V$ $dI_S/dt=50A/\mu s$	-	24	-	ns	
Reverse Recovery Charge	Q_{rr}		-	12	-	nC	
NOTE 1) * : Pulse Test : Pulse width <300 μs , Duty cycle < 2%							

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Fig1. $V_{DS} - I_D$

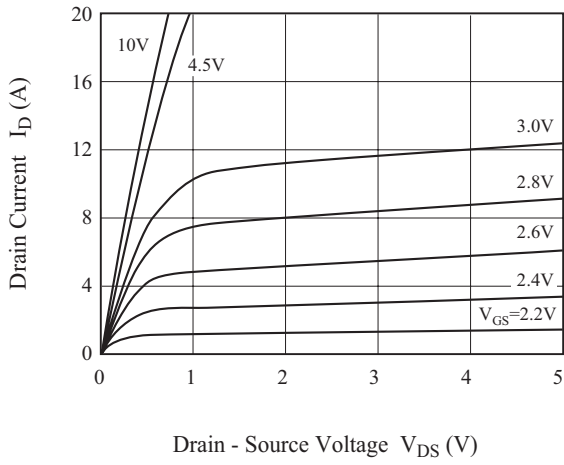


Fig2. $R_{DS(ON)} - I_D$

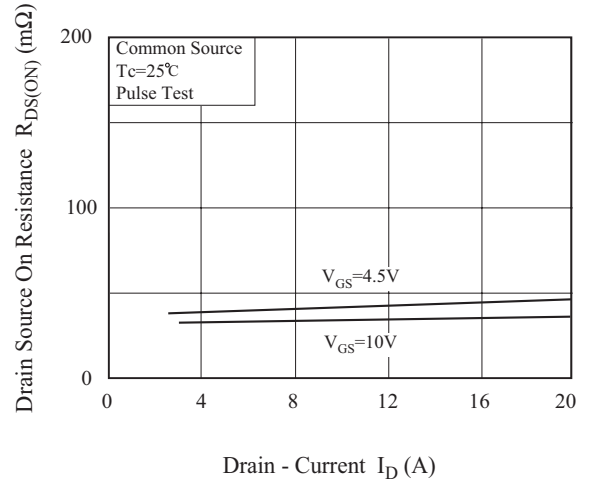


Fig3. $I_D - V_{GS}$

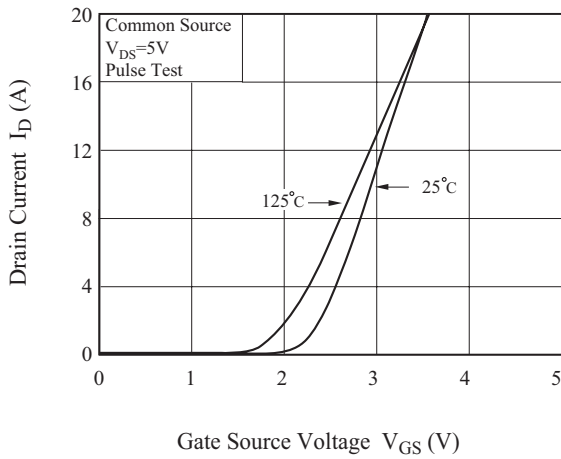


Fig4. $R_{DS(ON)} - T_j$

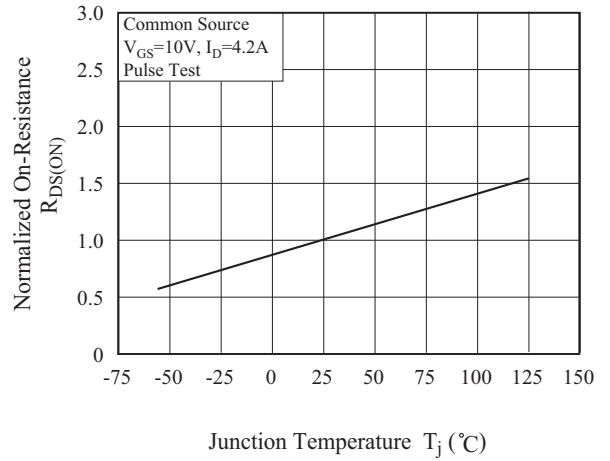


Fig5. $V_{th} - T_j$

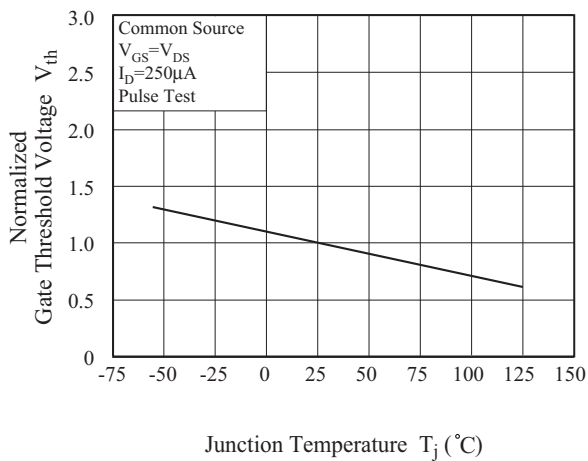
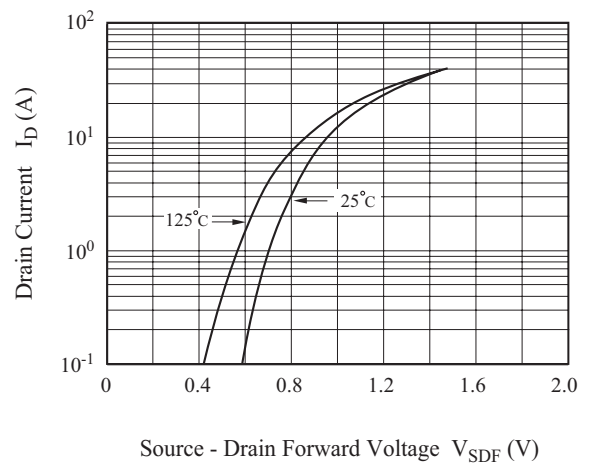


Fig6. $I_S - V_{SDF}$



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Fig7. Safe Operation Area

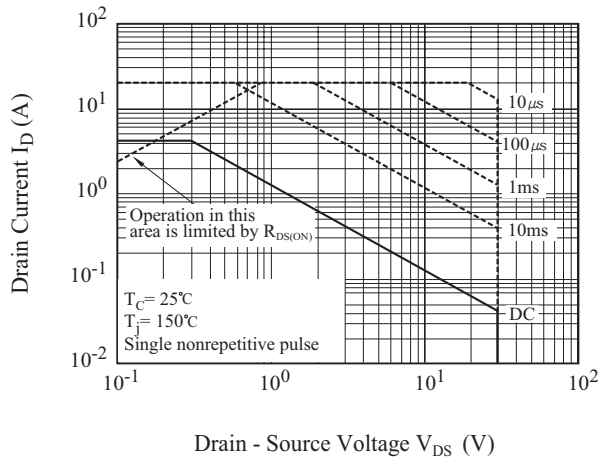


Fig8. Transient Thermal Response Curve

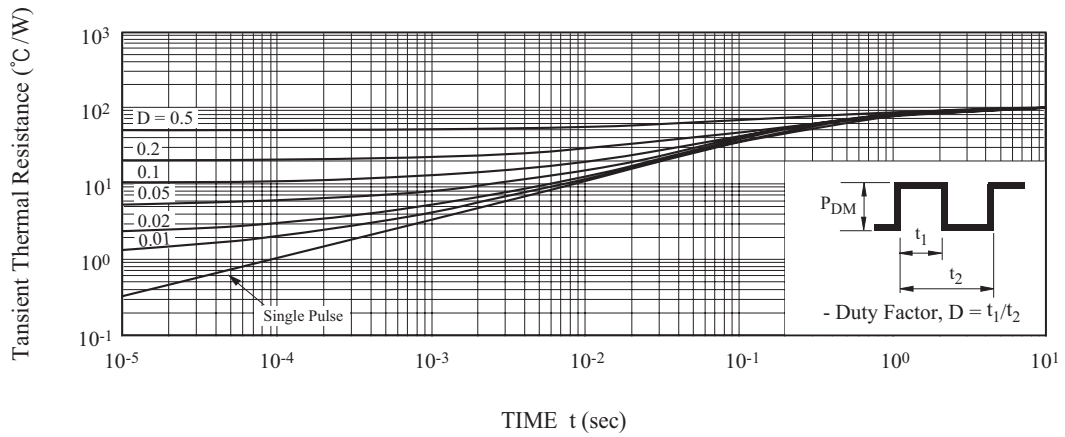


Fig9. Gate Charge Circuit and Wave Form

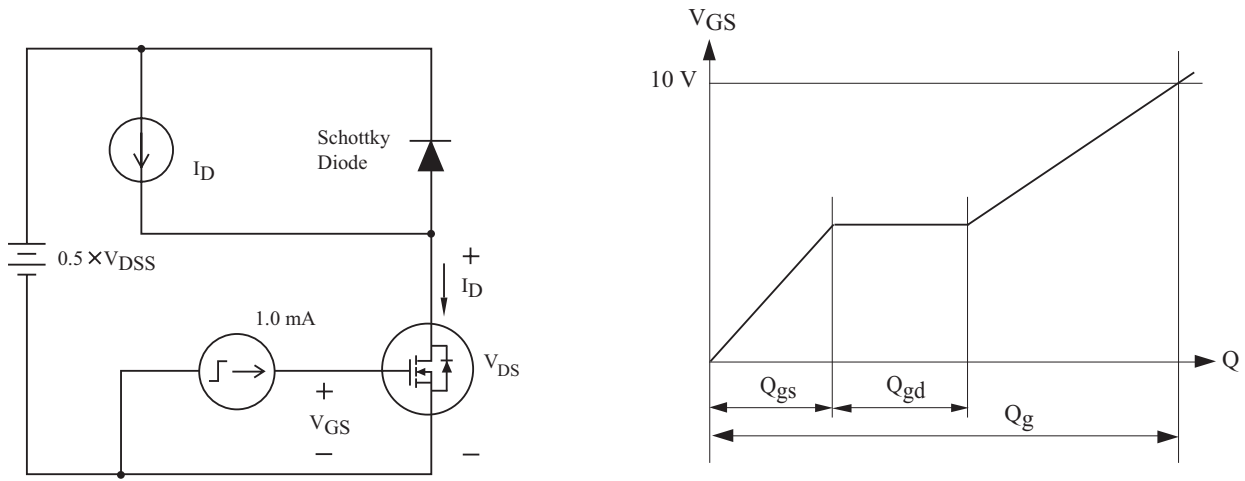


Fig10. Resistive Load Switching

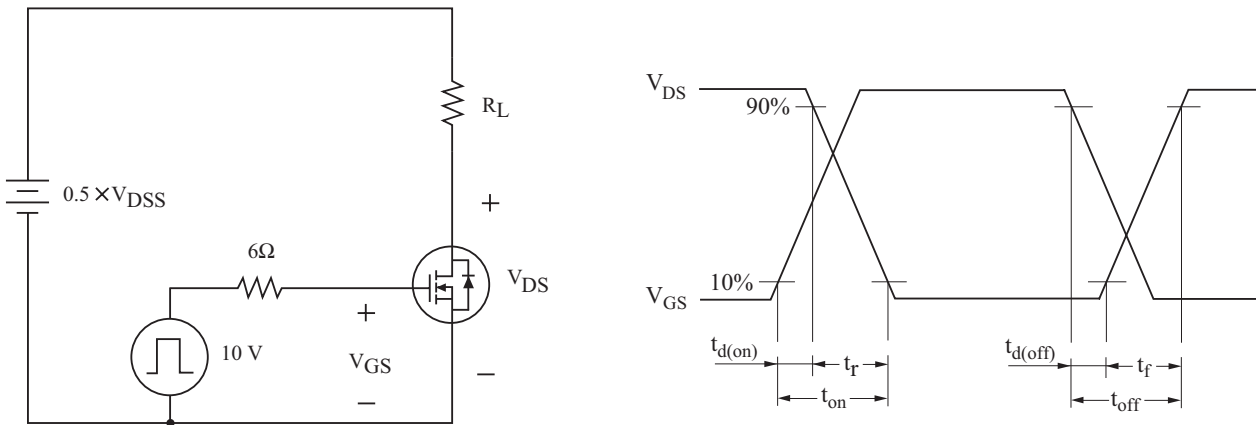


Fig11. Source - Drain Diode Reverse Recovery and dv/dt

